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		6,383,597	05/07/02	Fullerto	n et al.						
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A. M	Bruenger et al., "Ion projection lithography for resistless patterning of thin magnetic films", 25th International										
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B.M	•	1, 2000, pp. 7004-6.	Little maknesse tum-	s by ion beam irradiation", J.	Appl. Pays., (U	SA), Vol. 87, 1	No. 9, Pt. 1-3, May					
P.M		Corporate Associates, "Physics Helps Redesign Dow Chemical," 39 The Industrial Physicist, April 1999, American Institute of Physics, page 1.										
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